



MMBTA92

PNP SILICON TRANSISTOR

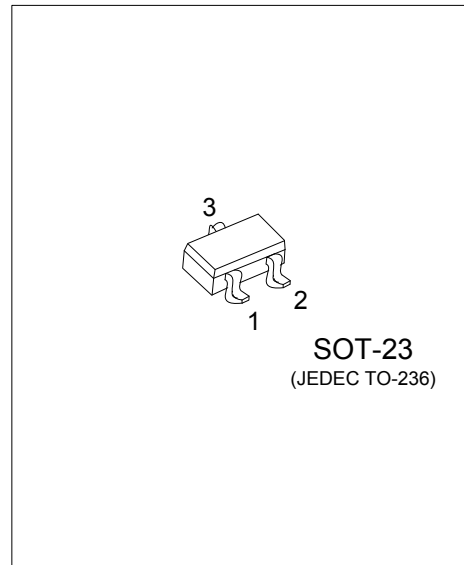
HIGH VOLTAGE PNP TRANSISTOR

DESCRIPTION

The UTC **MMBTA92** are high voltage PNP transistors, designed for telephone signal switching and for high voltage amplifier.

FEATURES

- * High Collector-Emitter voltage: $V_{CE0} = -300V$
- * Collector Dissipation: $P_{C(MAX)} = 350mW$



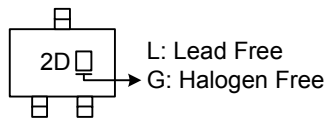
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
MMBTA92L-AE3-R	MMBTA92G-AE3-R	SOT-23	B	E	C	Tape Reel

Note: Pin Assignment: B: Base E: Emitter C: Collector

<p>MMBTA92G-AE3-R</p> <p>(1) Packing Type (2) Package Type (3) Green Package</p>	<p>(1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



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■ ABSOLUTE MAXIMUM RATINGS (Operating temperature range applies unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	-300	V
Collector-Emitter Voltage		V_{CEO}	-300	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		I_C	-500	mA
Collector Dissipation	$T_A=25^\circ\text{C}$	P_C	350	mW
	$T_C=25^\circ\text{C}$		1.5	W
	Derate Above $T_a > 25^\circ\text{C}$		12	mW/°C
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-40 ~ +150	°C

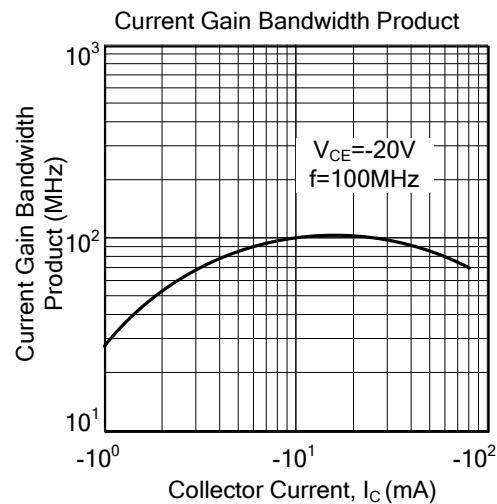
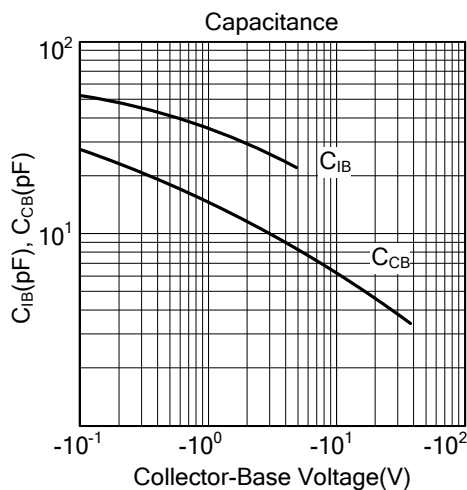
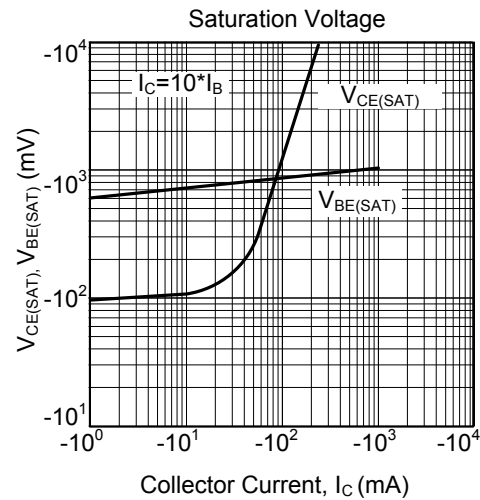
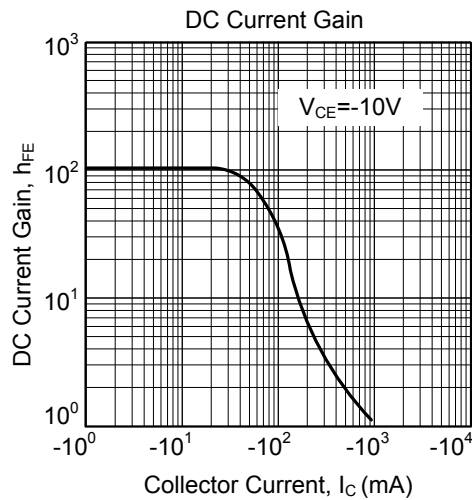
Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-100\mu\text{A}, I_E=0$	-300			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-1\text{mA}, I_B=0$	-300			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-200\text{V}, I_E=0$			-0.25	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-3\text{V}, I_C=0$			-0.10	μA
DC Current Gain (Note)	h_{FE}	$V_{CE}=-10\text{V}, I_C=-1\text{mA}$	60			
		$V_{CE}=-10\text{V}, I_C=-10\text{mA}$	80			
		$V_{CE}=-10\text{V}, I_C=-30\text{mA}$	80			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)1}$	$I_C=-20\text{mA}, I_B=-2\text{mA}$			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)1}$	$I_C=-20\text{mA}, I_B=-2\text{mA}$			-0.90	V
Current Gain Bandwidth Product	f_T	$V_{CE}=-20\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	50			MHz
Collector Base Capacitance	C_{cb}	$V_{CB}=-20\text{V}, I_E=0, f=1\text{MHz}$			6	pF

Note: Pulse test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycles $\leq 2\%$, $V_{CE(SAT)1} \leq 200\text{mV}$ (Class SIN).

TYPICAL CHARACTERISTICS



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